

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Bong-Cheol Kim  
Serial No. : To be Assigned  
Filed : To be Assigned  
For : APPARATUS AND METHOD FOR FORMING SINGLE  
CRYSTALLINE NITRIDE SUBSTRATE USING HYDRIDE  
VAPOR PHASE EPITAXY AND LASER BEAM

#3a  
D. Scott  
7-31-02

PRELIMINARY AMENDMENT

Assistant Commissioner of Patents

Washington, D.C. 20231

Sir:

Preliminary to the examination of the above-identified application, please  
make the following amendment to the claims:

In the Claims:Cancel claims 1 to 12.Add the following new claims:

add 257  
a

13. An apparatus for forming a nitrogen compound semiconductor  
substrate, the apparatus comprising:

a reacting chamber for forming a single crystalline nitride film on a parent  
substrate;

a heating chamber connected to the reacting chamber within a processing  
channel, wherein the single crystalline nitride film is separated from the parent substrate  
by laser beam illumination at a higher temperature than a room temperature; and